

ABSTRACT OF THE DISCLOSURE

A Cu thin film deposition equipment of a semiconductor device is disclosed for improving deposition speed of a Cu thin film and lowering its corresponding cost. This equipment includes a load lock carrying out the steps before and after wafer processes, an aligner carrying out alignment so that a wafer reaches a desired position, a de-gas chamber removing residue such as gas produced on a surface of a wafer, and a feeding chamber provided with a robot placing the wafer in/out of each chamber. A pre-cleaning chamber cleaning the inside and the outside of a pattern using plasma on a wafer fed by the feeding chamber, a barrier metal deposition chamber, an adhesion glue layer (AGL) flash Cu deposition chamber, a CECVD deposition chamber, and a plasma treatment chamber are also provided with the equipment.